

Excellent Integrated System Limited

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Infineon Technologies SIDC09D60F6

For any questions, you can email us directly: sales@integrated-circuit.com





SIDC09D60F6

Fast switching diode

Features:

- 600V Emitter Controlled technology 70 μm
 chip
- soft , fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

 power modules and discrete devices



Applications:

SMPS, resonant applications, drives

Chip Type	V_{R}	I F	Die Size	Package
SIDC09D60F6	600V	30A	3 x 3 mm ²	sawn on foil

Mechanical Parameters

3 x 3			
9	mm²		
2.518 x 2.518			
70	μm		
150	mm		
1612			
Photoimide			
3200 nm AlSiCu			
Ni Ag –system suitable for epoxy and soft solder die bonding			
Electrically conductive glue or solder			
Al, ≤250μm			
Ø 0.65mm; max 1.2mm			
Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C			
	9 2.518 x 2.518 70 150 1612 Photoimide 3200 nm AlSiCu Ni Ag –system suitable for epoxy and soft solder die bond Electrically conductive glue or solder Al, ≤250µm Ø 0.65mm; max 1.2mm Store in original container, in dry nitrogen, in		

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Datasheet of SIDC09D60F6 - DIODE GEN PURP 600V 30A WAFER

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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	<i>T</i> _{vj} = 25 °C	600	V
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	A
Maximum repetitive forward current	I _{FRM}	<i>T</i> _{vj} < 150°C	60	
Junction temperature range	T _{vj}		-40+175	°C
Operating junction temperature	T _{vj}		-40+150	°C
Dynamic ruggedness ²⁾	P _{max}	$I_{\text{Fmax}} = 60\text{A}, \ V_{\text{Rmax}} = 600\text{V}, \ T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW

¹⁾ depending on thermal properties of assembly

Static Characteristic (tested on wafer), $T_{vj} = 25 \,^{\circ}\text{C}$

Parameter	Symbol	Conditions	Value			Unit
raiailletei	Symbol	Conditions	min.	typ.	max.	Oilit
Reverse leakage current	I_{R}	V _R =600V			27	μA
Cathode-Anode breakdown Voltage	V_{BR}	I _R =1.5mA	600			V
Diode forward voltage	V_{F}	/ _F =30A		1.6		V

Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

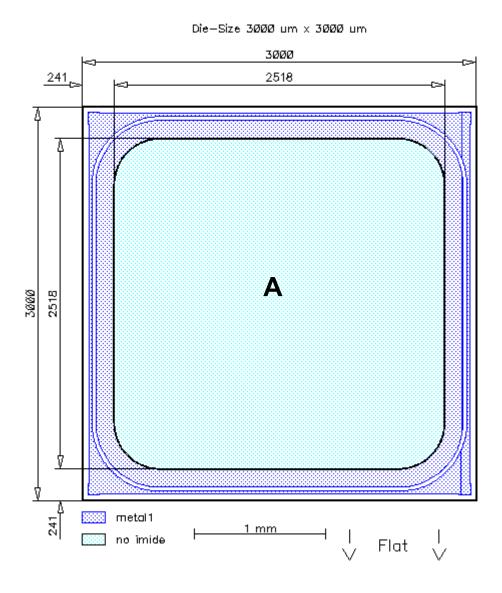
²⁾ not subject to production test - verified by design/characterisation





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Chip Drawing



A: Anode pad

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Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date
2.2	Max. possible chips per wafer change to 1612 pcs	03.09.2010

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